

SANYO

No.2266A

2SB1270/2SD1906

PNP/NPN Epitaxial Planar Type
Silicon Transistors

HIGH-CURRENT SWITCHING APPLICATIONS

Applications

- Suitable for relay drivers, high-speed inverters, converters, and other general high-current switching applications

Features

- Suitable for sets whose height is restricted
- Low collector to emitter saturation voltage
- Large current capacity

(): 2SB1270

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

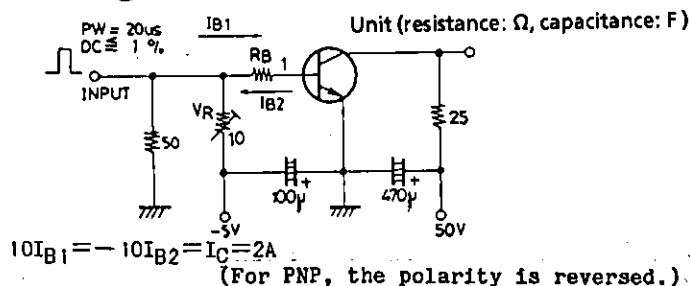
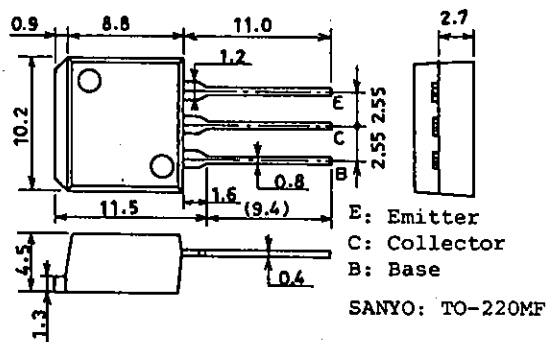
			unit
Collector to Base Voltage	V_{CB0}	(-)90	V
Collector to Emitter Voltage	V_{CE0}	(-)80	V
Emitter to Base Voltage	V_{EB0}	(-)6	V
Collector Current	I_C	(-)5	A
Peak Collector Current	i_{cp}	(-)9	A
Collector Dissipation	P_C	1.65	W
	$T_c=25^\circ\text{C}$	30	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=(-)80\text{V}, I_E=0$			(-)0.1	mA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=(-)4\text{V}, I_C=0$			(-)0.1	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=(-)2\text{V}, I_C=(-)1\text{A}$	70*		280*	
	$h_{FE(2)}$	$V_{CE}=(-)2\text{V}, I_C=(-)3\text{A}$	30			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)5\text{V}, I_C=(-)1\text{A}$		20		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)3\text{A}, I_B=(-)0.3\text{A}$			0.4 (-0.5)	V
C-B Breakdown Voltage	$V_{(BR)CB0}$	$I_C=(-)1\text{mA}, I_E=0$	(-)90			V
C-E Breakdown Voltage	$V_{(BR)CE0}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)80			V
E-B Breakdown Voltage	$V_{(BR)EB0}$	$I_E=(-)1\text{mA}, I_C=0$	(-)6			V
Turn-on Time	t_{on}	See specified Test Circuit.	(0.2)0.1			μs
Storage Time	t_{stg}	"	(0.7)1.2			μs
Fall Time	t_f	"	(0.2)0.4			μs

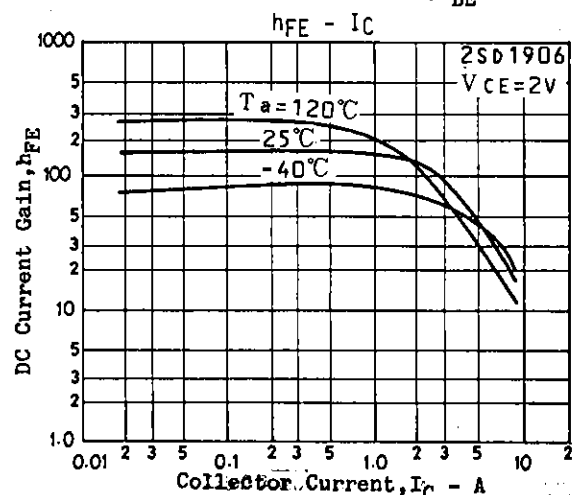
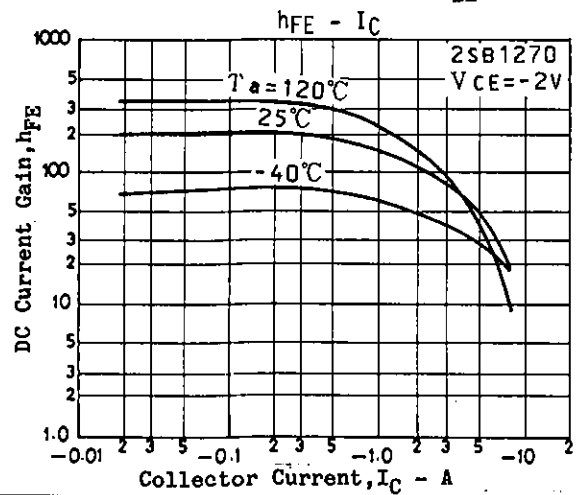
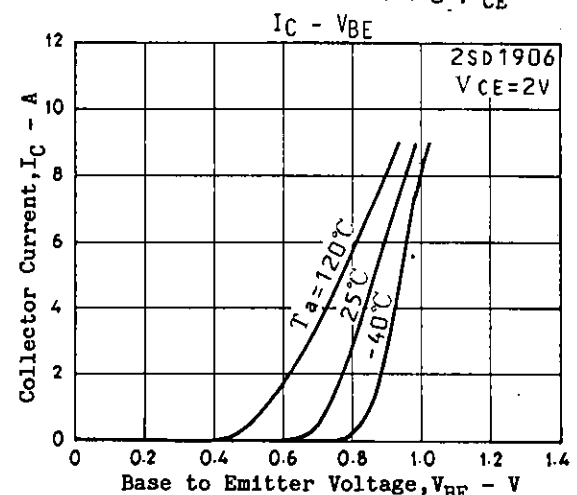
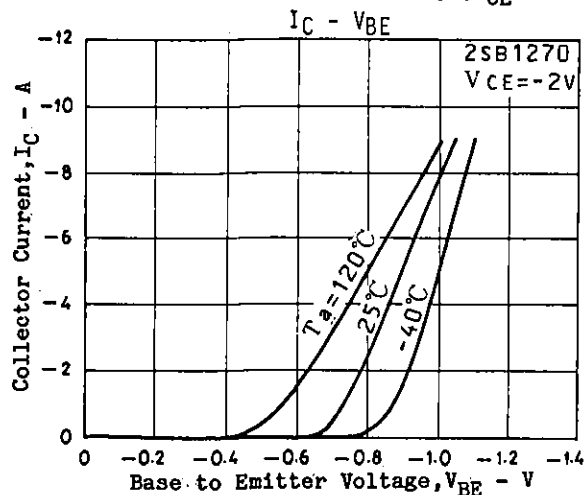
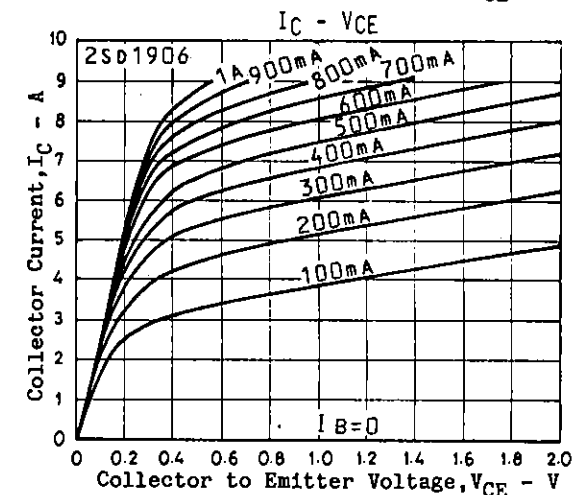
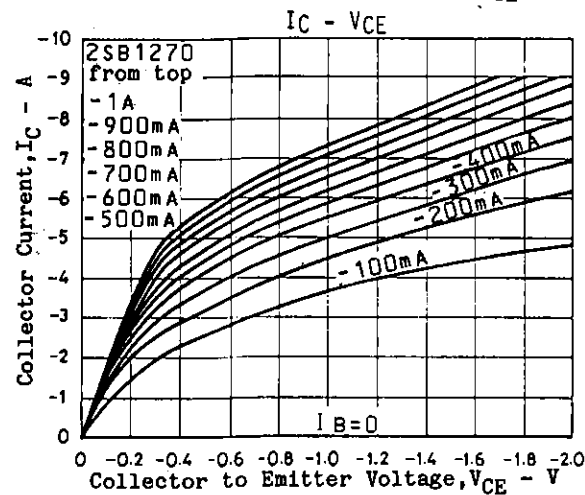
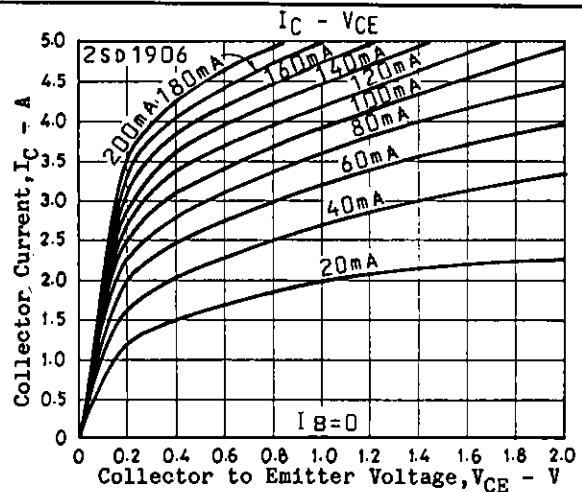
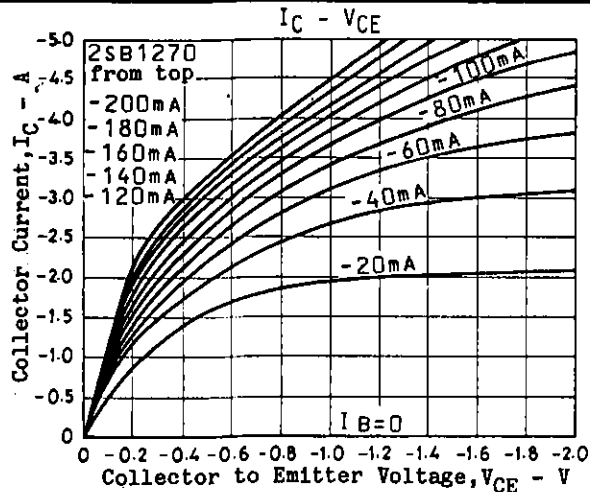
*: The 2SB1270/2SD1906 are classified by $1A h_{FE}$ as follows:

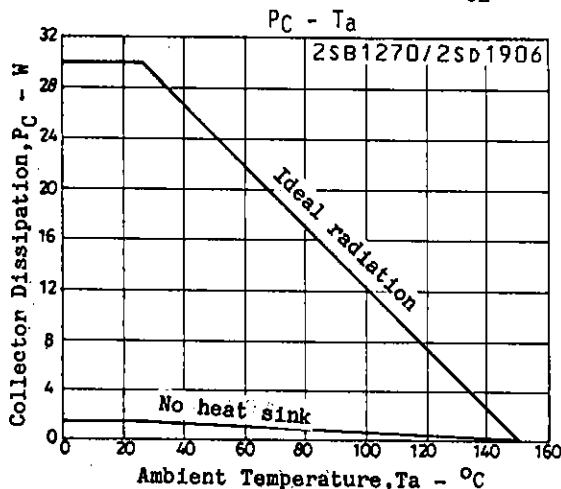
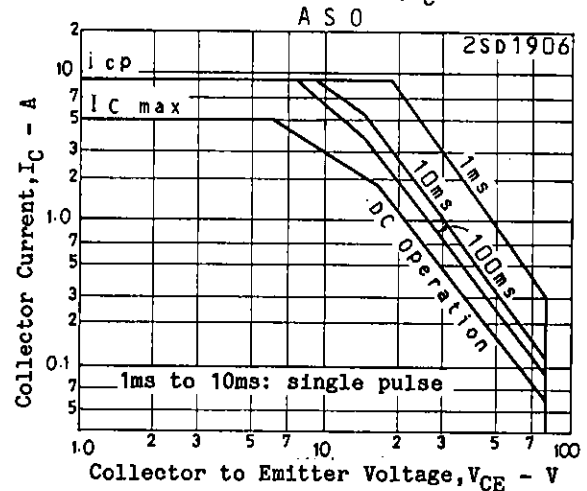
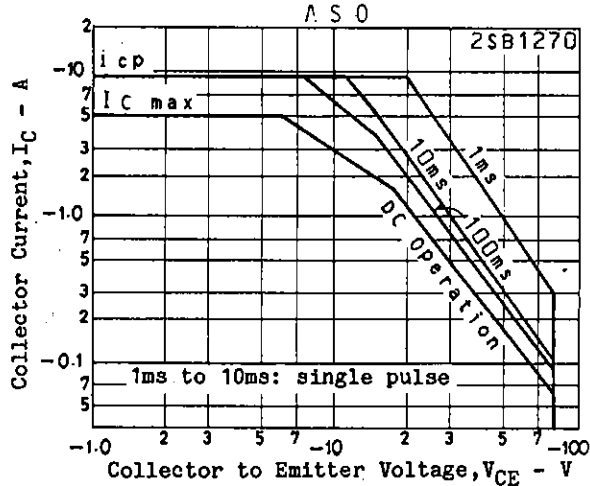
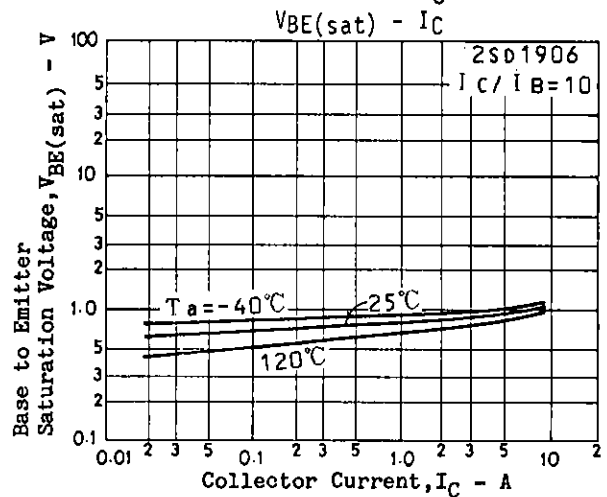
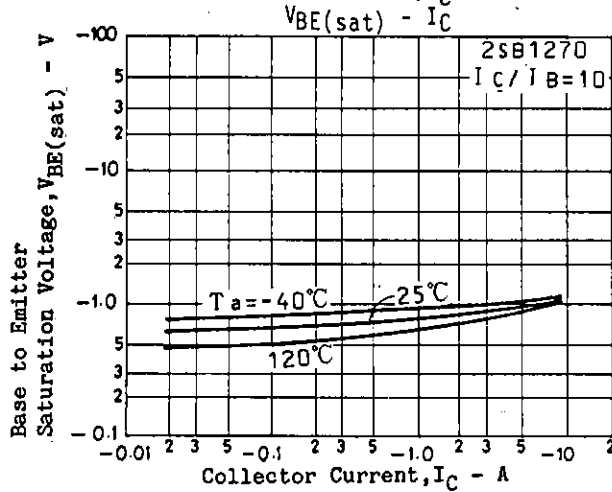
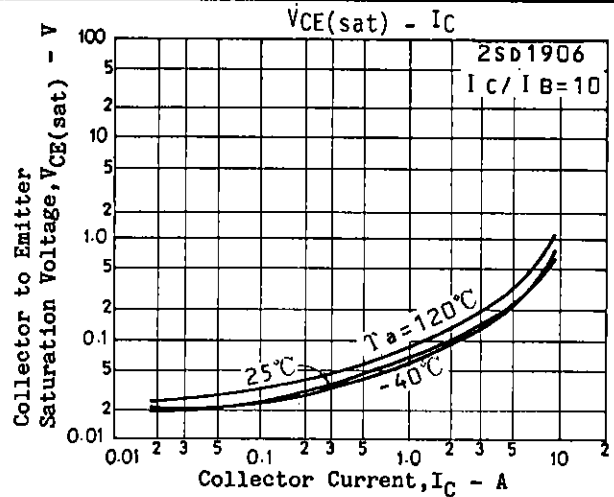
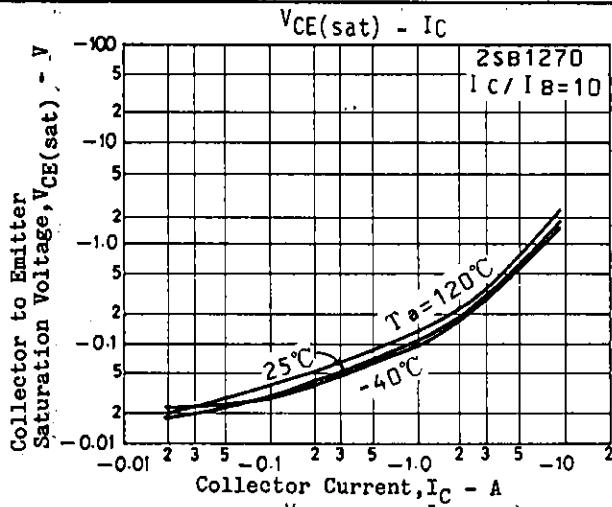
70	Q	140	100	R	200	140	S	280
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Switching Time Test Circuit**Package Dimensions 2049B**
(unit: mm)

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

D251MH/4097TA, TS No.2266-1/4





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